



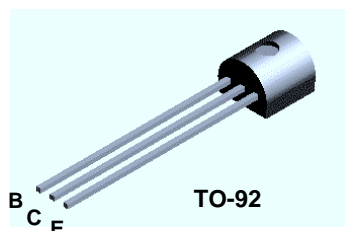
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## BC369



### PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.2 A. Sourced from Process 77.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	20	V
$V_{CES}$	Collector-Base Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
$I_C$	Collector Current - Continuous	1.5	A
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC369	
$P_D$	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier

(continued)

BC369

## Electrical Characteristics TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	20		V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ }\mu\text{A}, I_E = 0$	25		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ }\mu\text{A}, I_C = 0$	5.0		V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0$ $V_{CB} = 25 \text{ V}, I_E = 0, T_A = 150^\circ\text{C}$		10 1.0	$\mu\text{A}$ mA
$I_{EBO}$	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	$\mu\text{A}$

### ON CHARACTERISTICS

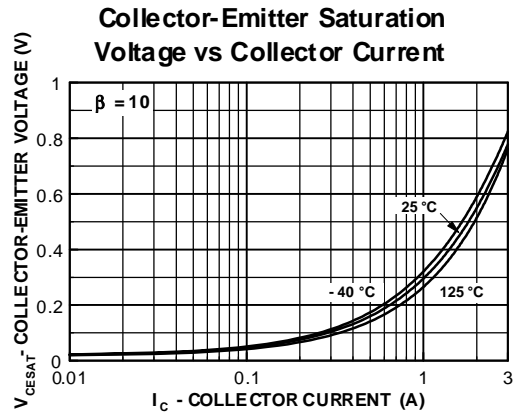
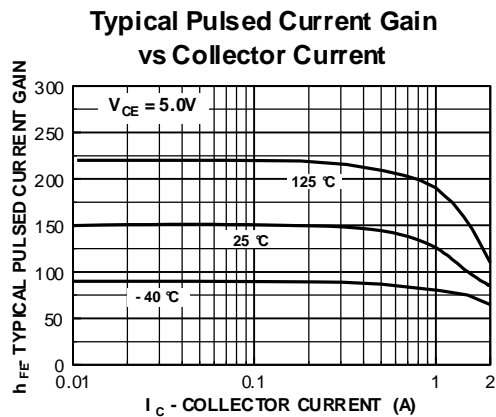
$h_{FE}$	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 0.5 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$	50 85 60	375	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ A}, I_B = 100 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$		1.0	V

### SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 35 \text{ MHz}$	45		MHz
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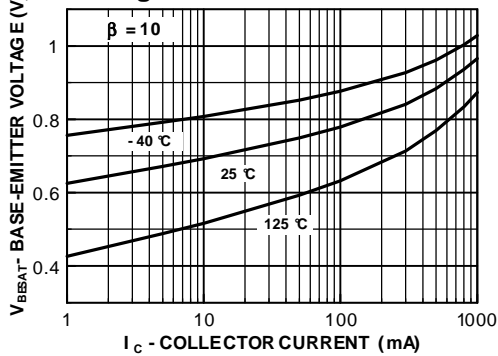
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

## Typical Characteristics

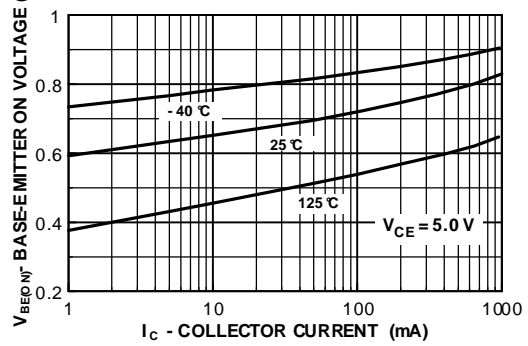


Typical Characteristics (continued)

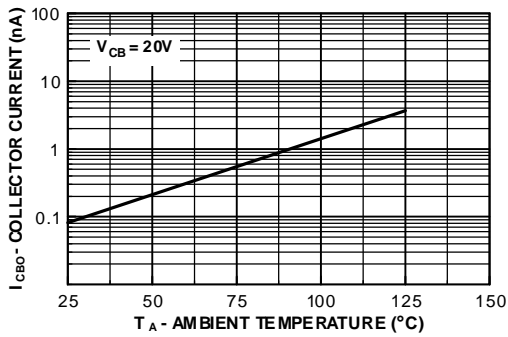
Base-Emitter Saturation Voltage vs Collector Current



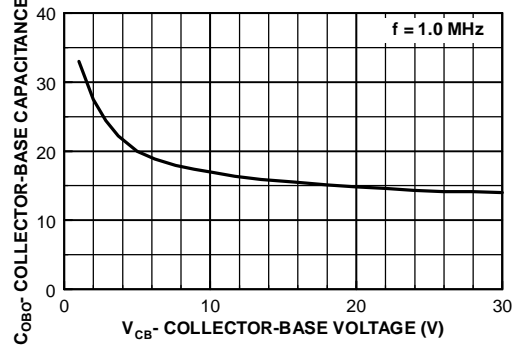
Base-Emitter ON Voltage vs Collector Current



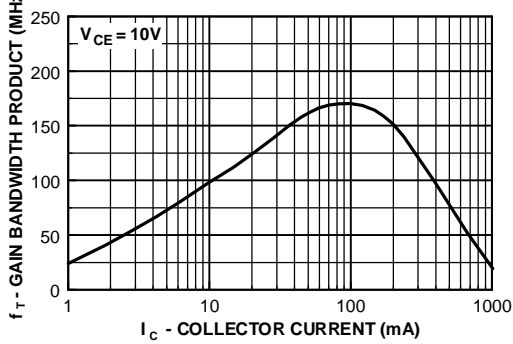
Collector-Cutoff Current vs Ambient Temperature



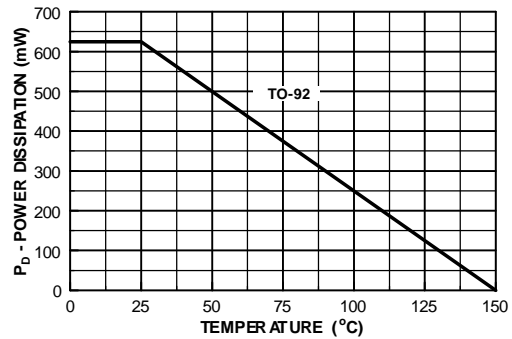
Collector-Base Capacitance vs Collector-Base Voltage



Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature



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